NPN RF POWER TRANSISTOR

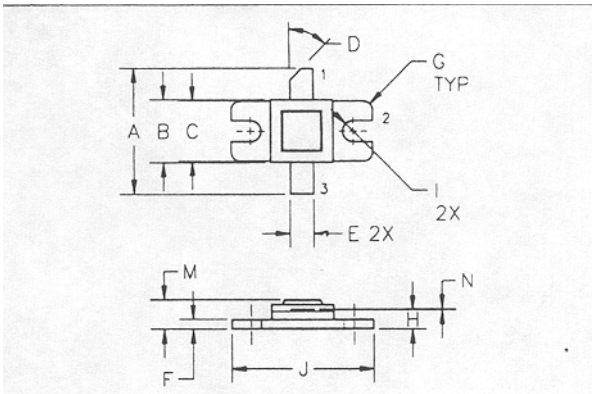
DESCRIPTION:

The **ASI MSC74518** is a Common Base Device Designed for Class C Applications in the 1.6 - 1.8 GHz bands.

FEATURES INCLUDE:

- Input/Output Matching
- Gold Metallization
- Hermetically Sealed Package
- Emitter Ballasting

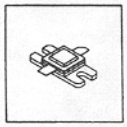
PACKAGE STYLE 400 2L FLG (Style 1)



DIM	MILLIMETER	TOL	INCHES	TOL
A	20.32	.76	.800	.050
B	10.16	.13	.400	.005
C	9.78	.13	.385	.005
D	45°	5°	45°	5°
E	3.81	.13	.150	.005
F	1.52	.13	.060	.005
G	1.52R	.13	.060R	.005
H	3.05	.13	.120	.005
I	3.30 DIA	.13	.130 DIA	.005
J	22.86	.13	.900	.005
K	16.51	.13	.650	.005
M	4.70	REF	.185	REF
N	0.13	.02	.005	.001

STYLE 1:
PIN1 = COLLECTOR
2 = BASE
3 = EMITTER

STYLE 2:
PIN1 = COLLECTOR
2 = EMITTER
3 = BASE



MAXIMUM RATINGS

I_C	1.0 A
V_{CBO}	40 V
P_{DISS}	20 W @ T_C = 25 °C
T_J	-55 °C to+200 °C
T_{STG}	-55 °C to+200 °C
θ_{JC}	9.0 °C/W

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 2.0 mA	40			V
BV_{EBO}	I_C = 2.0 mA	3.5			V
I_{CBO}	V_{CB} = 28 V			0.5	mA
h_{FE}	V_{CE} = 5 V I_C = 0.4 A	10		200	---
P_G	V_{CC} = 20 V P_{IN} = 1.0 W f = 1.7 - 2.0 GHz	6.6			dB
η_C	Pulse Width = 100 µS Duty Cycle = 10%	47			%